

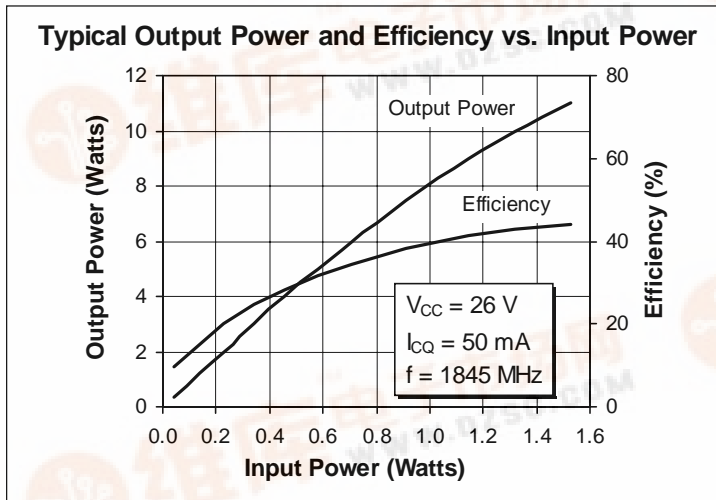


# PTB 20264 10 Watts, 1.8–1.9 GHz Cellular Radio RF Power Transistor

## Description

The 20264 is an NPN, common emitter RF power transistor intended for 26 Vdc class AB operation from 1.8 to 1.9 GHz. Rated at 10 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization ensure excellent device reliability. 100% lot traceability is standard.

- 26 Volt, 1.845 GHz Characteristics
  - Output Power = 10 Watts
  - Gain = 9.4 dB Typ at 5 Watts
- Class AB Characteristics
- Gold Metallization
- Silicon Nitride Passivated
- Surface Mountable
- Available in Tape and Reel



## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage, $R_{BE} = 10 \Omega$	$V_{CER}$	50	Vdc
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Emitter-Base Voltage (collector open)	$V_{EBO}$	4.0	Vdc
Collector Current (continuous)	$I_C$	2.0	Adc
Total Device Dissipation at $T_{flange} = 25^\circ C$ Above $25^\circ C$ derate by	$P_D$	30 0.173	Watts W/ $^\circ C$
Storage Temperature Range	$T_{STG}$	-40 to +150	$^\circ C$
Thermal Resistance ( $T_{flange} = 70^\circ C$ )	$R_{\theta JC}$	5.8	$^\circ C/W$



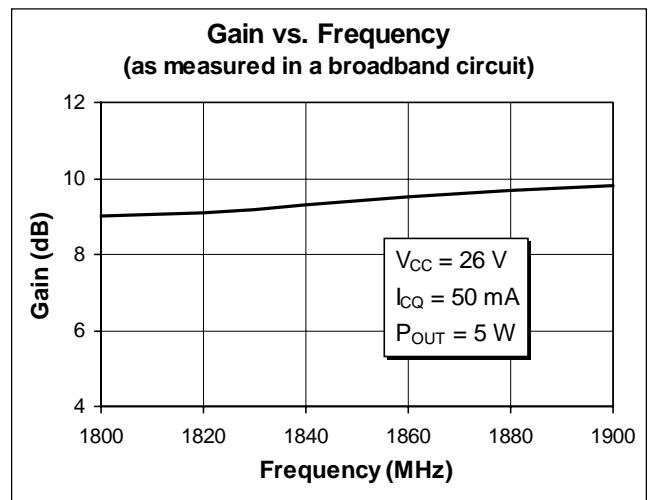
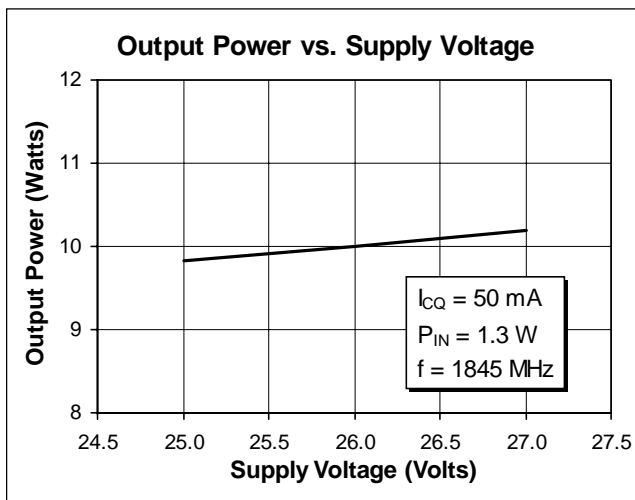
**Electrical Characteristics** (100% Tested)

Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$I_B = 0\text{ A}, I_C = 10\text{ mA}$	$V_{(BR)CEO}$	22	26	—	Volts
Breakdown Voltage C to E	$V_{BE} = 0\text{ V}, I_C = 10\text{ mA}$	$V_{(BR)CES}$	55	60	—	Volts
Breakdown Voltage E to B	$I_C = 0\text{ A}, I_E = 5\text{ mA}$	$V_{(BR)EBO}$	3.5	5	—	Volts
DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 250\text{ mA}$	$h_{FE}$	20	50	120	—

**RF Specifications** (100% Tested)

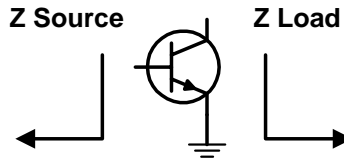
Characteristic	Symbol	Min	Typ	Max	Units
<b>Gain at <math>P_{OUT} = 5\text{ Watts}</math></b> ( $V_{CC} = 26\text{ Vdc}, I_{CQ} = 50\text{ mA}, f = 1805\text{ MHz}, 1845\text{ MHz}, 1880\text{ MHz}$ )	$G_{pe}$	9.0	9.4	—	dB
<b>Gain Compression at <math>P_{OUT} = 5\text{ Watts}</math></b> ( $V_{CC} = 26\text{ Vdc}, I_{CQ} = 50\text{ mA}, f = 1805\text{ MHz}, 1845\text{ MHz}, 1880\text{ MHz}$ )	—	—	—	0.2	dB
<b>Gain at <math>P_{OUT} = 10\text{ Watts}</math></b> ( $V_{CC} = 26\text{ Vdc}, I_{CQ} = 50\text{ mA}, f = 1845\text{ MHz}$ )	$G_{pe}$	8.4	—	—	dB
<b>Gain Compression at <math>P_{OUT} = 10\text{ Watts}</math></b> ( $V_{CC} = 26\text{ Vdc}, I_{CQ} = 50\text{ mA}, f = 1845\text{ MHz}$ )	—	—	—	0.8	dB
<b>Collector Efficiency at <math>P_{OUT} = 10\text{ Watts}</math></b> ( $V_{CC} = 26\text{ Vdc}, I_{CQ} = 50\text{ mA}, f = 1845\text{ MHz}$ )	$\eta_C$	40	—	—	%
<b>Load Mismatch Tolerance</b> ( $V_{CC} = 26\text{ Vdc}, P_{OUT} = 10\text{ W}, I_{CQ} = 50\text{ mA}, f = 1845\text{ MHz}$ —all phase angles at frequency of test)	$\Psi$	—	—	5:1	—

**Typical Performance**



**Impedance Data** (data shown for fixed-tuned broadband circuit)

$V_{CC} = 26 \text{ Vdc}$ ,  $P_{OUT} = 10 \text{ W}$ ,  $I_{CQ} = 50 \text{ mA}$



Frequency	Z Source		Z Load	
	R	jX	R	jX
1805	11.4	2.6	12.2	8.1
1850	11.0	3.7	12.2	9.6
1880	10.9	4.3	12.4	10.6

